UHBS15-2

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI UHBS15-2** is Designed for Class C, FM Base Station Applications up to 960 MHz.

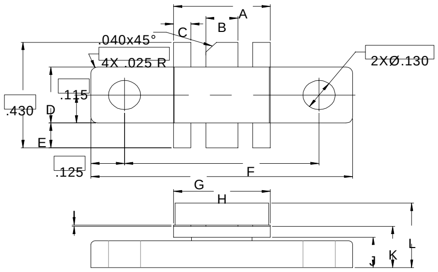
FEATURES:

- Internal Input Matching Network
- P_G = 9.0 dB at 15 W/960 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	2.0 A
V_{CBO}	55 V
V_{CEO}	28 V
V_{CES}	55 V
V_{EBO}	4.0 V
P_{DISS}	50 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	3.0 °C/W

PACKAGE STYLE .230 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.355 / 9.02	.365 / 9.27
B	.115 / 2.92	.125 / 3.18
C	.075 / 1.91	.085 / 2.16
D	.225 / 5.72	.235 / 5.97
E	.090 / 2.29	.110 / 2.79
F	.720 / 18.29	.730 / 18.54
G	.970 / 24.64	.980 / 24.89
H	.355 / 9.02	.365 / 9.27
I	.004 / 0.10	.006 / 0.15
J	.120 / 3.05	.130 / 3.30
K	.160 / 4.06	.180 / 4.57
L	.230 / 5.84	.260 / 6.60

ORDER CODE: ASI10669

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 50 mA	28			V
BV_{CES}	I_C = 50 mA R_{BE} = 10 Ω	55			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CBO}	V_{CB} = 15 V			2.5	mA
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	30		200	---
C_{ob}	V_{CB} = 24 V f = 1.0 MHz			25	pF
P_G	V_{CE} = 24 V P_{OUT} = 15 W f = 960 GHz	9.5			dB
η_C			50		%